

Bi-directional 12V Low Capacitance ESD Protector

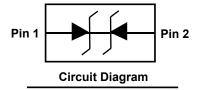
Description

The PESDNC2XD12VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one unidirectional line in applications where arrays are not practical.



Feature

- DFN0603-2L package
- Replacement for MLV(0201)
- Bidirectional configurations
- Response time is typically < 1 ns</p>
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)



Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

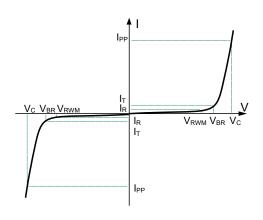


Mechanical Characteristics

- Mounting position: Any
- ➤ Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN0603-2L without plating

Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V_{BR}	Breakdown Voltage @ I _⊺		
lτ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ I _{PP}		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
I _F	Forward Current		
V _F	Forward Voltage @ I _F		



Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	ol Conditions		Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				12	V
Breakdown Voltage	V _{BR}	I _t = 1mA	13	15		V
Reverse Leakage Current	I _R	V _{RWM} = 12V T=25℃			1	μA
Clamping Voltage	VcL	I _{PP} =16A t _p =100ns		17		V
Clamping Voltage	Vc	I _{PP} = 1A t _P = 8/20μs		16	18	V
Clamping Voltage	Vc	$I_{PP} = 3A$ $t_P = 8/20 \mu s$		20	23	V
Junction Capacitance	C _j	V _R =0V f = 1MHz	6	8	10	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Operating Temperature	TJ	-55 to 150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$
Peak pulse power(t _p =8/20us)	P _{PK}	60	W
Peak pulse current(t _p =8/20us)	I _{PP}	3	А

Typical Characteristics

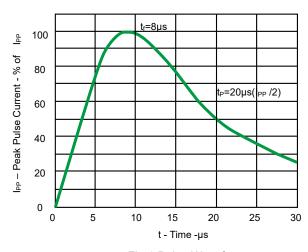


Fig 1.Pulse Waveform

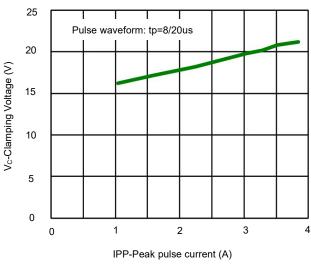


Fig 3. Clamping voltage vs. Peak pulse current

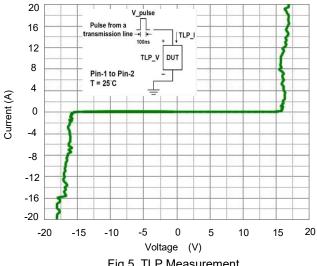


Fig 5. TLP Measurement

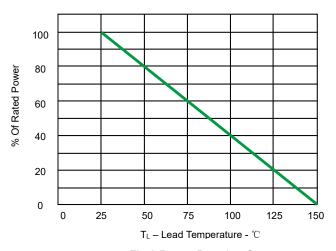


Fig 2.Power Derating Curve

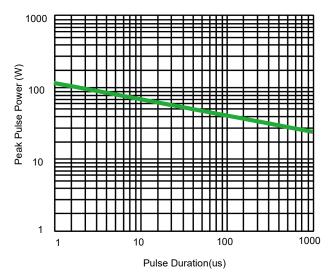


Fig 4. Non-Repetitive Peak Pulse Power vs. Pulse time

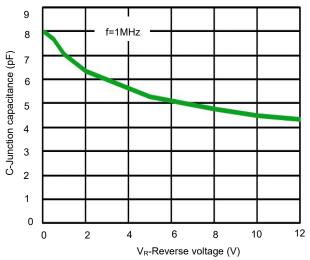
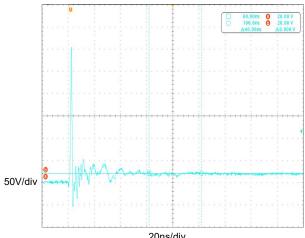


Fig 6. Capacitance vs. Reveres voltage



20ns/div Fig 7. ESD clamping voltage (IEC61000-4-2 +8KV contact)

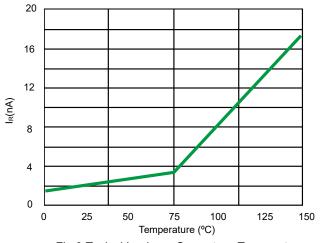
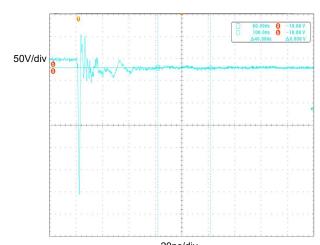


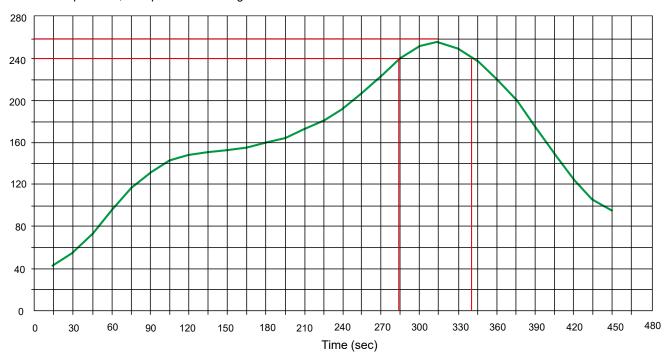
Fig 9.Typical Leakage Current vs. Temperature



20ns/div Fig 8. ESD clamping voltage (IEC61000-4-2-8KV contact)

Solder Reflow Recommendation

Peak Temp=257℃, Ramp Rate=0.802deg. ℃/sec

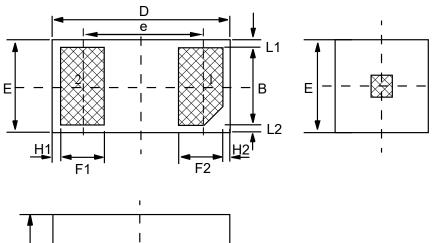


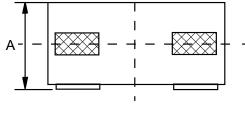
PCB Design

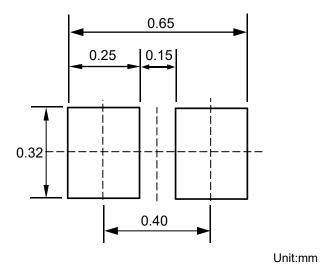
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- > Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN0603-2L)







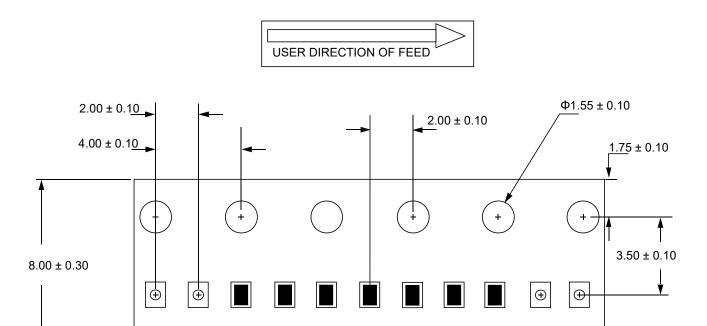
Suggested PCB Layout

Dim	Millimeters			
	MIN	Тур.	MAX	
Α	0.270	0.300	0.340	
В	0.200	0.250	0.300	
D	0.550	0.600	0.650	
E	0.250	0.300	0.350	
е	-	0.350	-	
F1	0.130	0.180	0.230	
F2	0.130	0.180	0.230	
L1	0.015	0.030	0.045	
L2	0.015	0.030	0.045	
H1	0.030	0.045	0.060	
H2	0.030	0.045	0.060	

Ordering information

Device	Package	Reel	Shipping
PESDNC2XD12VB	DFN0603-2L (Pb-Free)	7"	10000 / Tape & Reel

Load with information



Unit: mm

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